NSM80101MT1G

NPN Transistor with Dual Series Switching Diode

Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD Control Board
- High Speed Switching
- High Voltage Switching

MAXIMUM RATINGS – PNP TRANSISTOR

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	80	Vdc
Collector – Base Voltage	V_{CBO}	80	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	500	mAdc

MAXIMUM RATINGS – SWITCHING DIODE

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	V
Forward Current	I_F	200	mA
Non−Repetitive Peak Forward Current (Square Wave, T_J = 25°C prior to surge) t < 1 sec t = 1 μsec	I_{FSM}	 1.0 20	A
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ESD RATINGS

Rating		Class	Value
Electrostatic Discharge	HBM MM	3A M4	4000 V ≤ Failure < 8000 V Failure > 400 V

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) @ T_A = 25°C Derate above 25°C	P_D	400	mW mW/°C
Thermal Resistance from Junction−to−Ambient (Note 1)	$R_{\theta JA}$	313	°C/W
Total Device Dissipation FR−5 Board (Note 2) T_A = 25°C Derate above 25°C	P_D	270	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	463	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 650 mm^2 pad, 2.0 oz Cu.
2. FR−5 = 10 mm^2 pad, 2.0 oz Cu.

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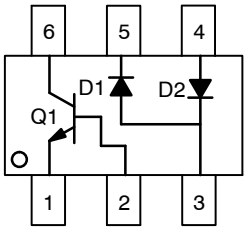
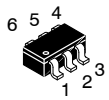
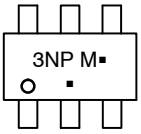
NPN Transistor with Dual Series Switching Diode





SC−74
CASE 318F

MARKING DIAGRAM



3NP = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NSM80101MT1G	SC−74 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Q1: NPN TRANSISTOR
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) (I_C = 1.0 mA, I_B = 0)	$V_{(BR)CEO}$	80	–	V
Emitter – Base Breakdown Voltage (I_E = 100 μA, I_C = 0)	$V_{(BR)EBO}$	6.0	–	V
Collector Cutoff Current (V_{CE} = 60 V, I_B = 0)	I_{CES}	–	0.1	μA
Collector Cutoff Current (V_{CB} = 80 V, I_E = 0)	I_{CBO}	–	0.1	μA
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I_C = 10 mA, V_{CE} = 1.0 V)	h_{FE}	120	–	–
Collector – Emitter Saturation Voltage (I_C = 100 mA, I_B = 10 mA)	$V_{CE(sat)}$	–	0.3	V
Base – Emitter Saturation Voltage (I_C = 10 mA, V_{CE} = 5.0 Vdc)	$V_{BE(sat)}$	–	1.2	V
SMALL–SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 V, f = 100 MHz)	f_T	150	–	MHz

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

D1, D2: SWITCHING DIODE (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage	$V_{(BR)}$	75	–	V
Reverse Voltage Leakage Current (V_R = 75 V) (V_R = 20 V, T_J = 150°C) (V_R = 75 V, T_J = 150°C)	I_R	– – –	1.0 30 100	μA
Diode Capacitance (V_R = 0 V, f = 1.0 MHz)	C_D	–	2.0	pF
Forward Voltage (I_F = 1.0 mA) (I_F = 10 mA) (I_F = 50 mA) (I_F = 150 mA)	V_F	– – – –	715 855 1000 1250	mV
Reverse Recovery Time (I_F = I_R = 10 mA, $i_{R(REC)}$ = 1.0 mA, R_L = 100 Ω)	t_{rr}	–	6.0	ns
Forward Recovery Voltage (I_F = 10 mA, t_r = 20 ns)	V_{FR}	–	1.75	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

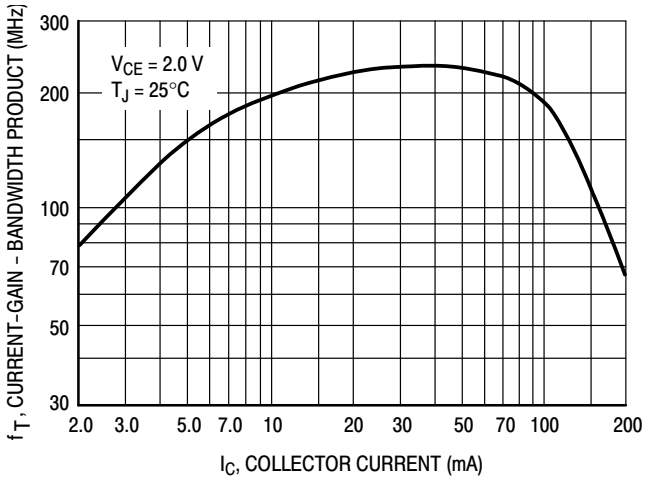


Figure 1. Current−Gain — Bandwidth Product

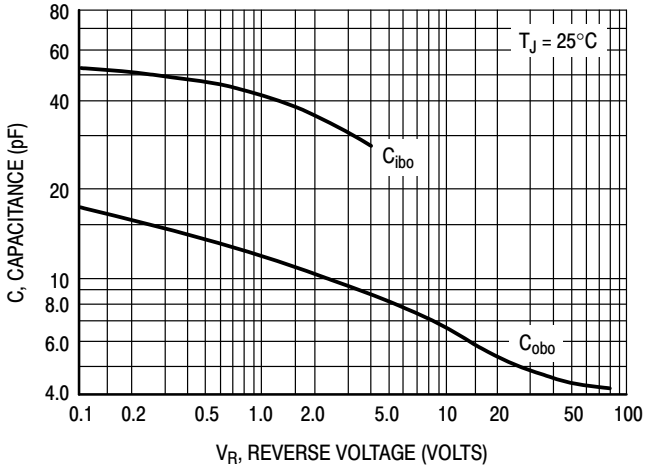


Figure 2. Capacitance

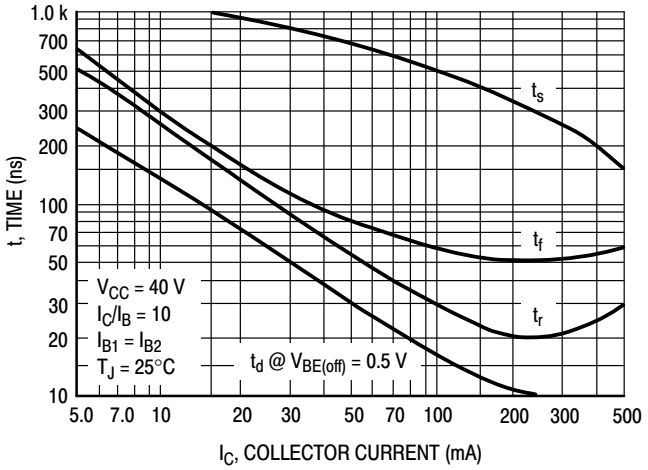


Figure 3. Switching Time

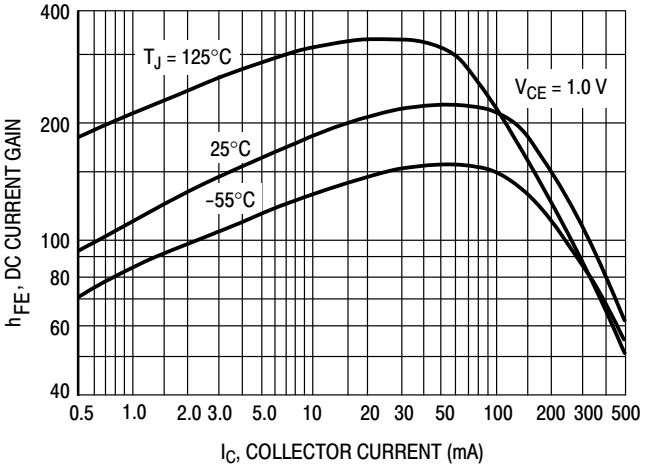


Figure 4. DC Current Gain

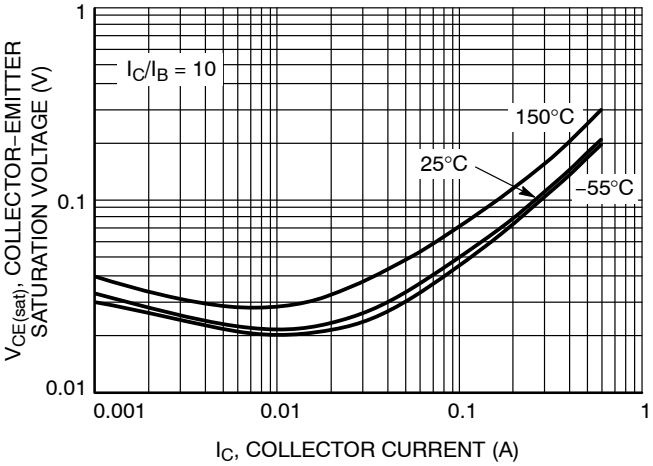


Figure 5. Collector Emitter Saturation Voltage vs. Collector Current

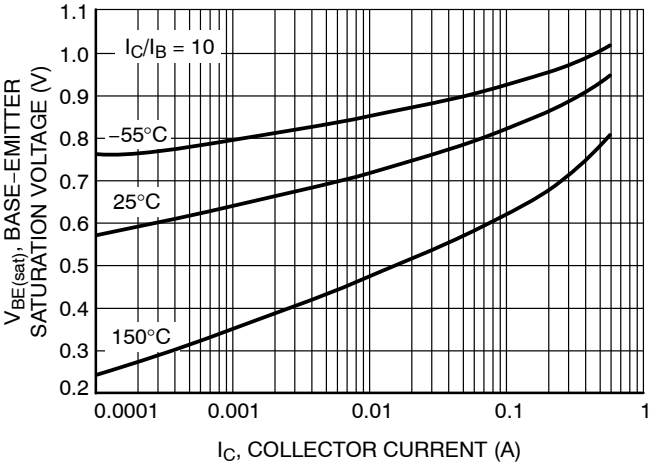


Figure 6. Base Emitter Saturation Voltage vs. Collector Current

TYPICAL CHARACTERISTICS

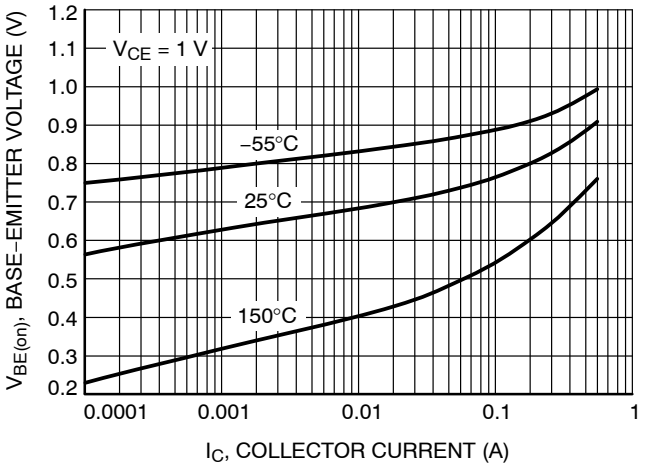


Figure 7. Base Emitter Voltage vs. Collector Current

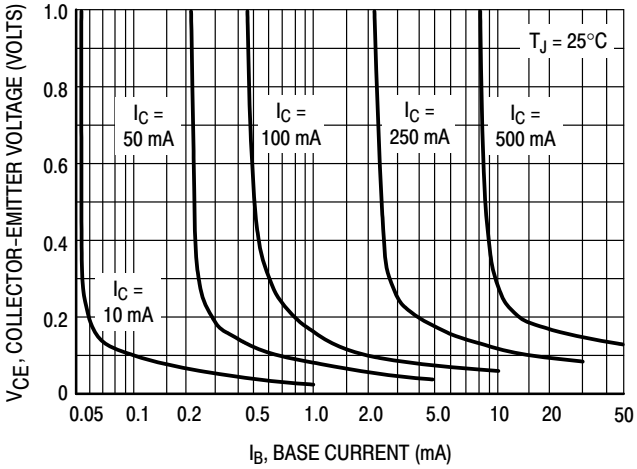


Figure 8. Collector Saturation Region

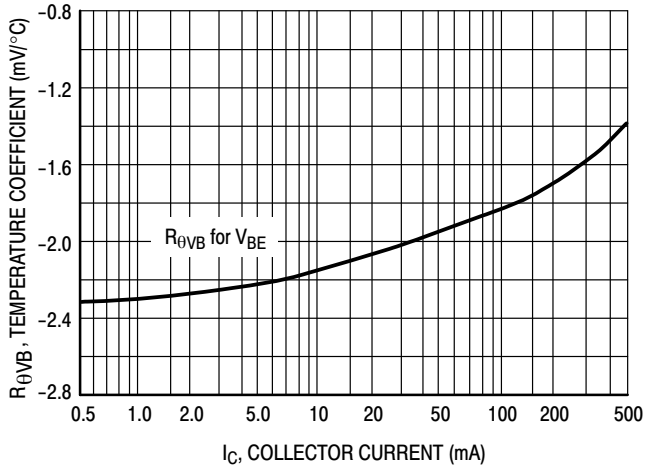


Figure 9. Base−Emitter Temperature Coefficient

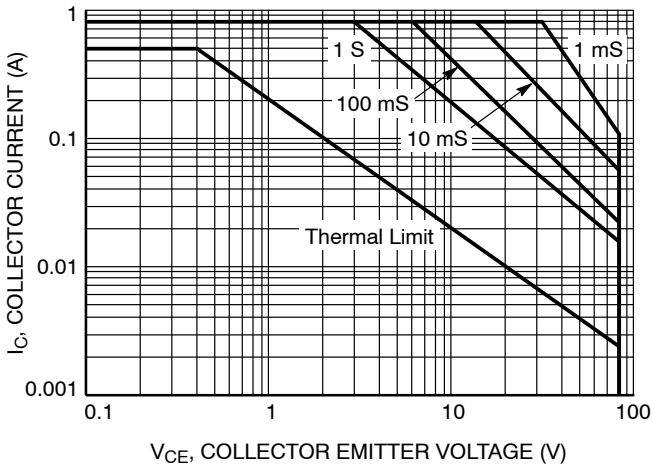


Figure 10. Safe Operating Area

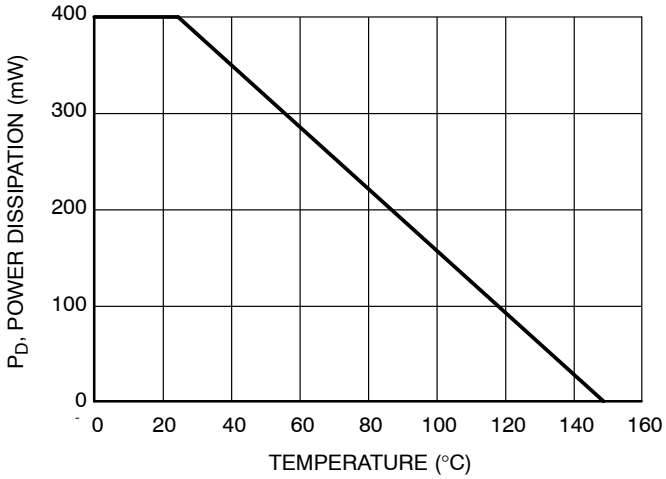


Figure 11. Operating Temperature Derating

TYPICAL CHARACTERISTICS

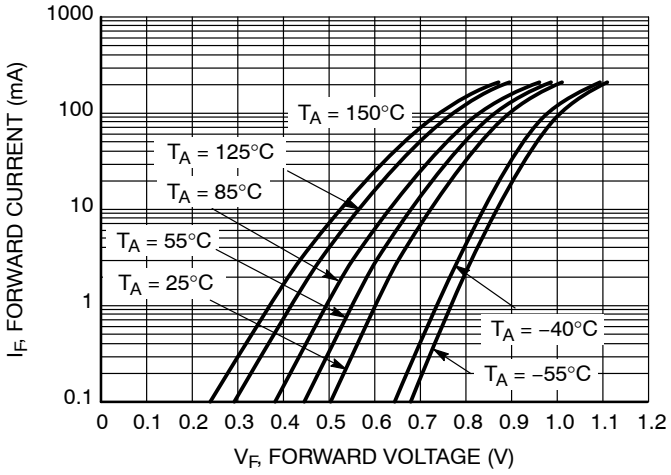


Figure 12. Forward Voltage

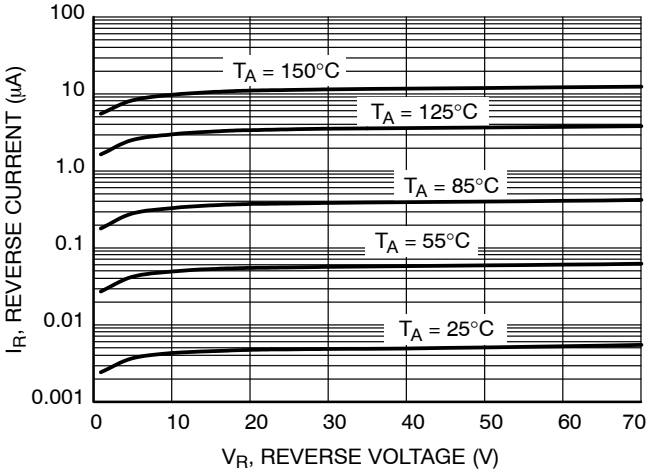


Figure 13. Leakage Current

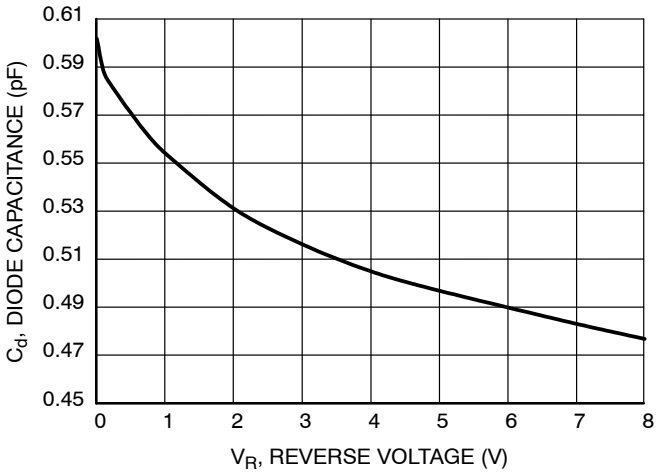


Figure 14. Capacitance

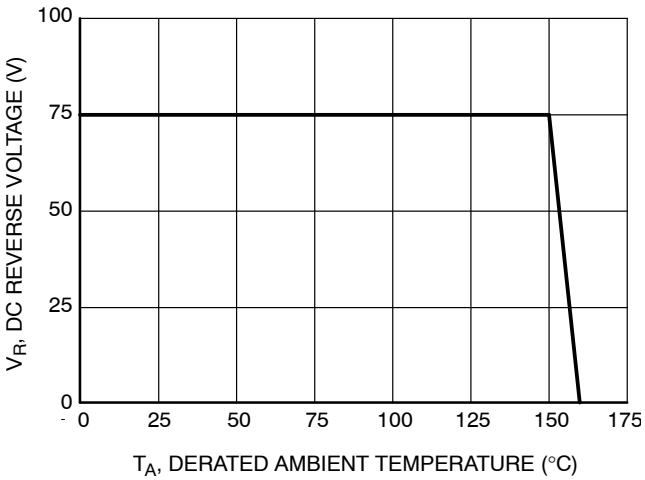
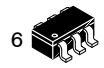


Figure 15. Diode Power Dissipation Curve

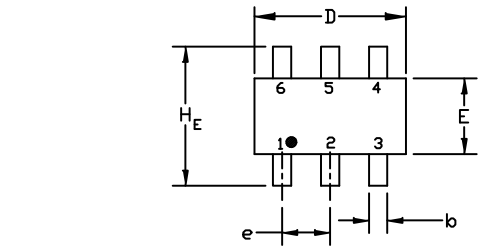
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



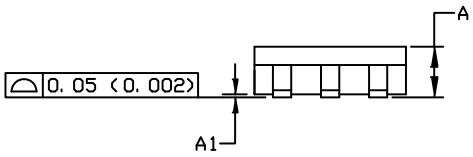
SCALE 2:1

SC−74
CASE 318F
ISSUE P

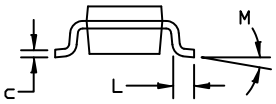
DATE 07 OCT 2021



TOP VIEW



SIDE VIEW

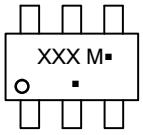


END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
H_E	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0°	---	10°	0°	---	10°

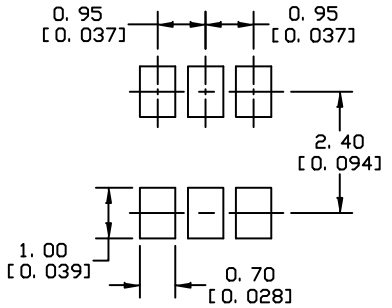
GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE

STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3

STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1

STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE

STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR

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